

# Memristive technologies for data storage, computation, communication

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Neuromorphic-computing-based adaptive learning using ion dynamics in flexible energy storage devices. National Science Review, 2022, 9, .	9.5	31
2	Wear-out and breakdown of Ta <sub>2</sub> O <sub>5</sub> /Nb:SrTiO <sub>3</sub> stacks. Solid-State Electronics, 2022, 198, 108462.	1.4	0
3	Modeling the Variability of Au/Ti/h-BN/Au Memristive Devices. IEEE Transactions on Electron Devices, 2023, 70, 1533-1539.	3.0	5
4	Electrode Engineering in Memristors Development for Non-/Erasable Storage, Random Number Generator, and Synaptic Applications. , 2022, , .		0
5	Tunable full-color emission phosphors: Enhanced security application via a patterned 3-dimensions code. Ceramics International, 2023, 49, 345-356.	4.8	6
6	Parameter extraction techniques for the analysis and modeling of resistive memories. Microelectronic Engineering, 2022, 265, 111876.	2.4	9
7	Spiking neural networks based on two-dimensional materials. Npj 2D Materials and Applications, 2022, 6, .	7.9	20
8	A Statistical Study of Resistive Switching Parameters in Au/Ta/ZrO <sub>2</sub> (Y)/Ta <sub>2</sub> O <sub>5</sub> /TiN/Ti Memristive Devices. Physica Status Solidi (A) Applications and Materials Science, 2023, 220, .	1.8	2
9	Roles of Low-Dimensional Nanomaterials in Pursuing Human-Machine-Thing Natural Interaction. Advanced Materials, 2023, 35, .	21.0	4
10	The Impact of Electrostatic Interactions Between Defects on the Characteristics of Random Telegraph Noise. IEEE Transactions on Electron Devices, 2022, 69, 6991-6998.	3.0	4
11	Compact artificial neuron based on anti-ferroelectric transistor. Nature Communications, 2022, 13, .	12.8	31
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14	Emerging MXene-Based Memristors for In-Memory, Neuromorphic Computing, and Logic Operation. Advanced Functional Materials, 2023, 33, .	14.9	32
15	Thermal effects on TiN/Ti/HfO <sub>2</sub> /Pt memristors charge conduction. Journal of Applied Physics, 2022, 132, 194501.	2.5	1
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18	Pseudo-flexible resistive switching characteristics of nano-bowl-like NiO arrays on mica substrates. Applied Surface Science, 2023, 613, 155994.	6.1	2

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19	A High-Speed and High-Efficiency Diverse Error Margin Write-Verify Scheme for an RRAM-Based Neuromorphic Hardware Accelerator. IEEE Transactions on Circuits and Systems II: Express Briefs, 2023, 70, 1366-1370.	3.0	0
20	Parameter Extraction Methods for Assessing Device-to-Device and Cycle-to-Cycle Variability of Memristive Devices at Wafer Scale. IEEE Transactions on Electron Devices, 2023, 70, 360-365.	3.0	3
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